Abstracts

80 GHz distributed amplifiers with transferred-substrate heterojunction bipolar transistors

B. Agarwal, R. Pullela, Q. Lee, D. Mensa, J. Guthrie and M.J.W. Rodwell. "80 GHz distributed amplifiers with transferred-substrate heterojunction bipolar transistors." 1998 MTT-S International Microwave Symposium Digest 98.2 (1998 Vol. II [MWSYM]): 529-532.

We report distributed amplifiers with 80 GHz bandwidth, 6.7 dB gain and /spl sim/70 GHz bandwidth, 7.7 dB gain. These amplifiers were fabricated in the transferred-substrate heterojunction bipolar transistor integrated circuit technology. Transferred-substrate HBTs have very high f/sub max/ (>400 GHz) and have yielded distributed amplifiers with record gain-bandwidth product.

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